261-166

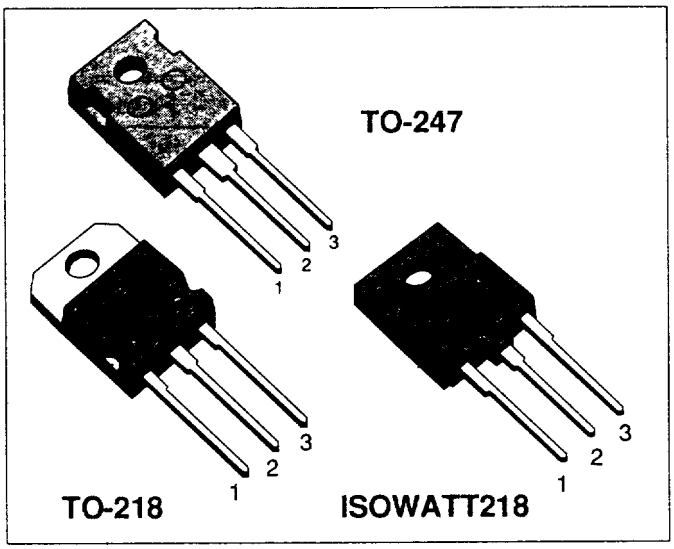
SGS-THOMSON MICROELECTRONICS

STH8N80/FI
STW8N80

N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STH8N80	800 V	< 1.2 Ω	8.2 A
STH8N80FI	800 V	< 1.2 Ω	5.1 A
STW8N80	800 V	< 1.2 Ω	8 2 A

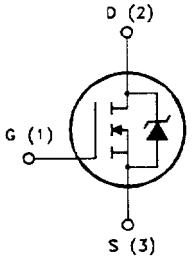
- TYPICAL $R_{DS(on)}$ = 0.98 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STH/STW8N80	STH8N80FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	800		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	800		V
V_{GS}	Gate-source Voltage	± 20		V
I_D	Drain Current (continuous) at T_c = 25 °C	8.2	5.1	A
I_D	Drain Current (continuous) at T_c = 100 °C	5.1	3.2	A
I_{DM}(•)	Drain Current (pulsed)	35	35	A
P_{tot}	Total Dissipation at T_c = 25 °C	180	70	W
	Derating Factor	1.44	0.56	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

THERMAL DATA

			TO-218/TO-247	ISOWATT218	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.69	1.78	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30		°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.1		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	8.2	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	800	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	18	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (T_c = 100 °C, pulse width limited by T_j max, $\delta < 1\%$)	4.5	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	800			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating x 0.8 T_c = 125 °C			250 1000	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V I_D = 4 A V_{GS} = 10V I_D = 4 A T_c = 100°C		0.98	1.2 2.4	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	8.2			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 4 A	4	7		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		2100 270 115	2700 350 150	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 400 V I_D = 4 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 3)		90 280	120 350	ns ns
$(di/dt)_{on}$	Turn-on Current Slope	V_{DD} = 640 V I_D = 8 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		145		A/µs
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 400 V I_D = 8 A V_{GS} = 10 V		125 12 65	170	nC nC nC

SWITCHING OFF

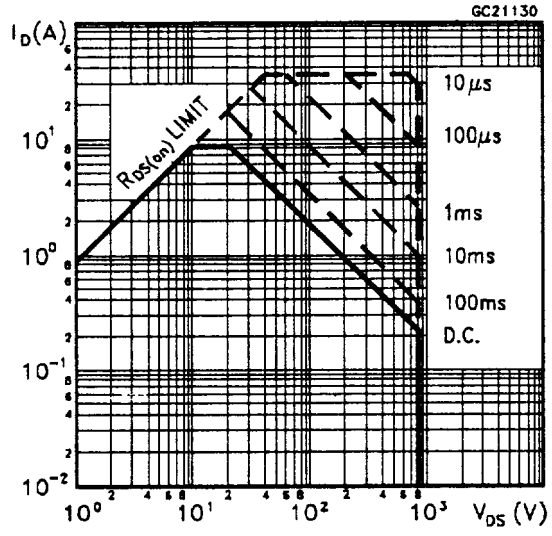
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 640 V I_D = 8 A R_G = 50 Ω V_{GS} = 10 V (see test circuit, figure 5)		160 50 235	200 65 300	ns ns ns

SOURCE DRAIN DIODE

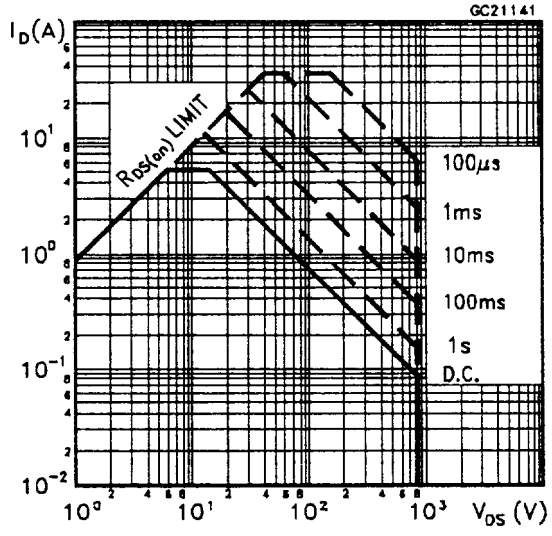
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				8.2 35	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 8.2 A V_{GS} = 0			2.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 8.2 A di/dt = 100 A/µs V_R = 100 V T_j = 150 °C (see test circuit, figure 5)		900 24.8 55		ns µC A

(*) Pulsed: Pulse duration = 300 µs, duty cycle 1 5 %
(•) Pulse width limited by safe operating area

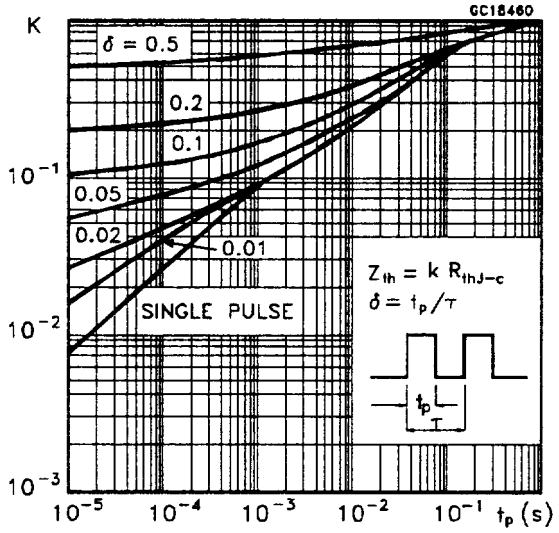
Safe Operating Areas For TO-218 and TO-247



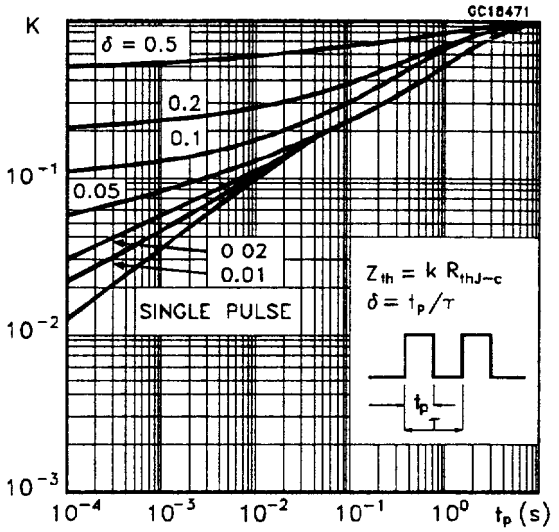
Safe Operating Areas For ISOWATT218



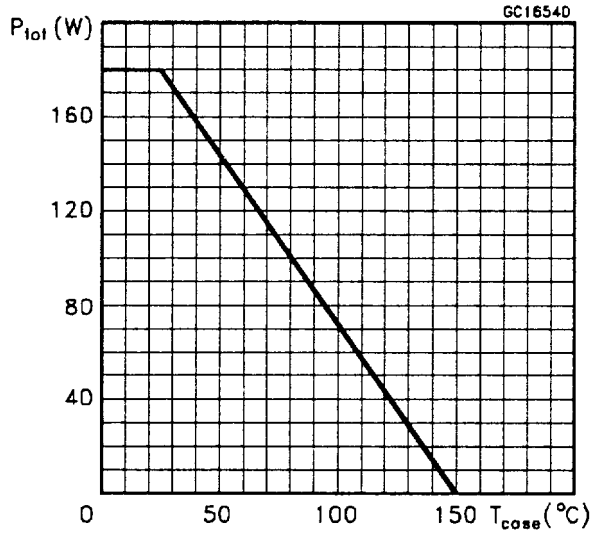
Thermal Impedeance For TO-218 and TO-247



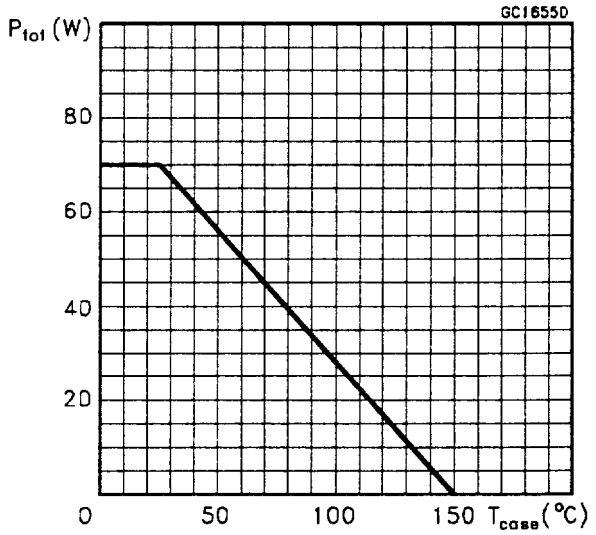
Thermal Impedance For ISOWATT218



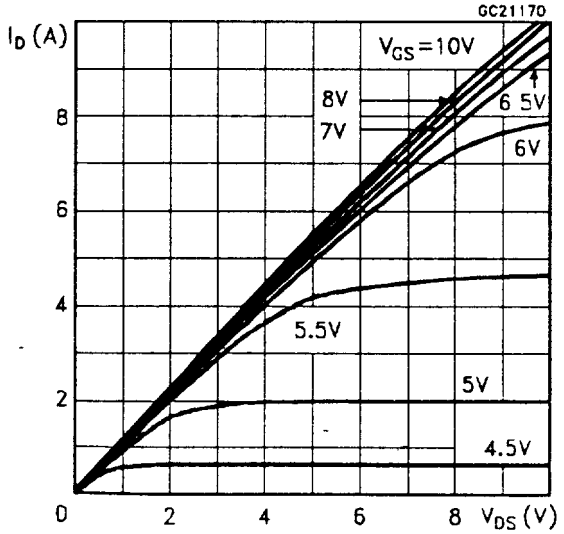
Derating Curve For TO-218 and TO-247



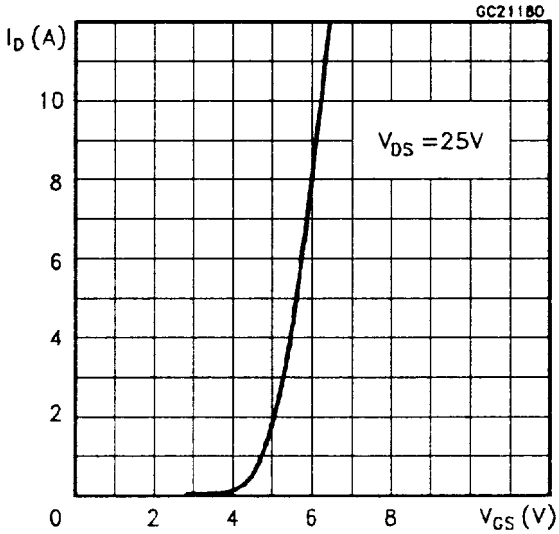
Derating Curve For ISOWATT218



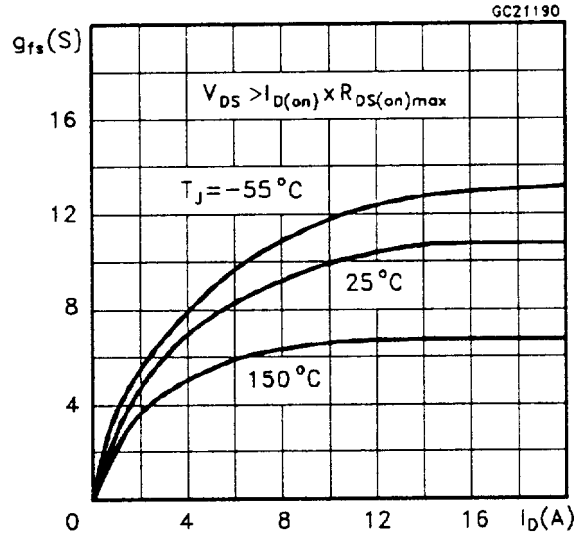
Output Characteristics



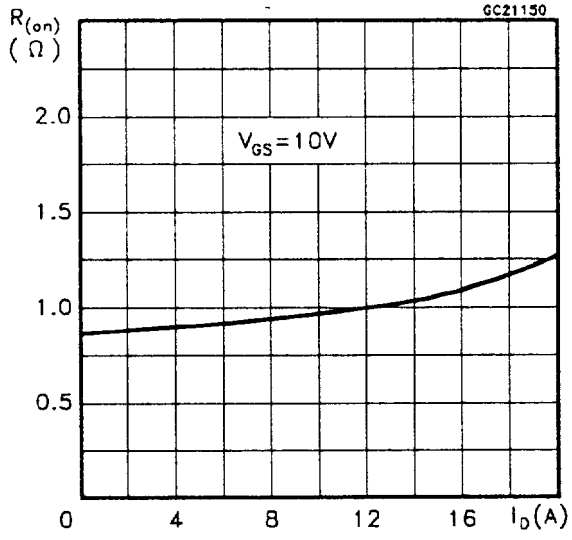
Transfer Characteristics



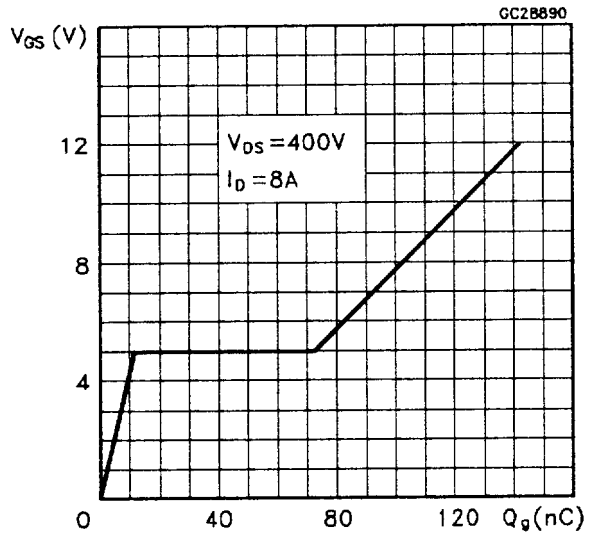
Transconductance



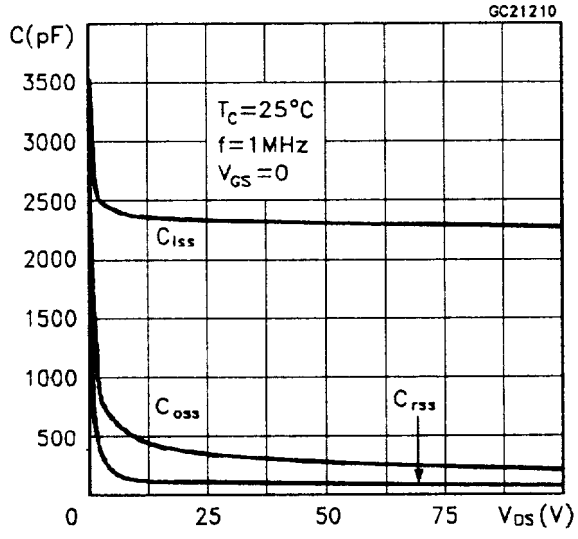
Static Drain-source On Resistance



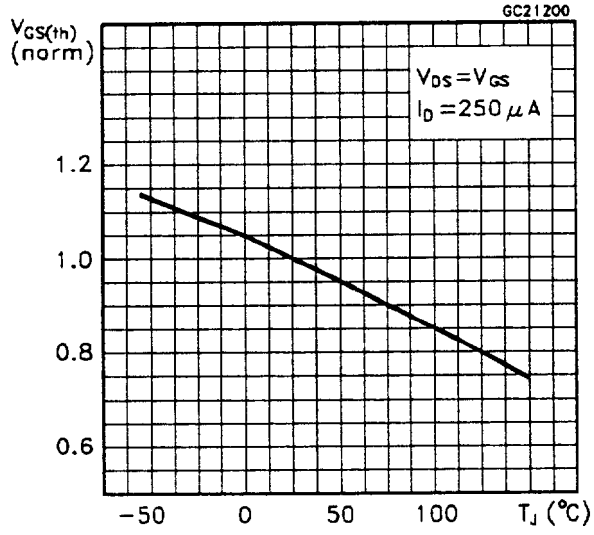
Gate Charge vs Gate-source Voltage



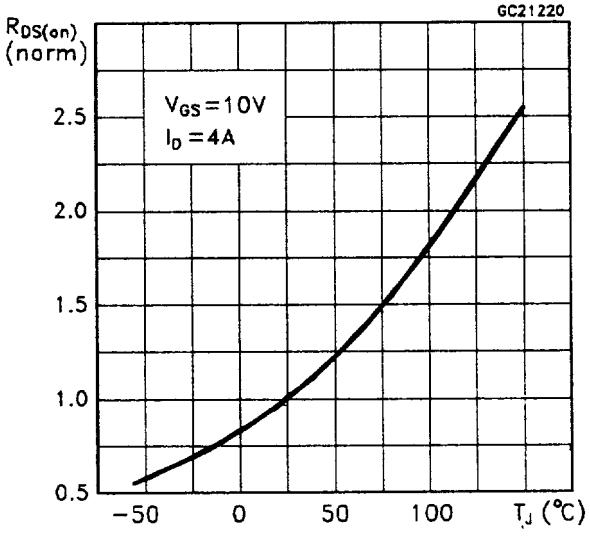
Capacitance Variations



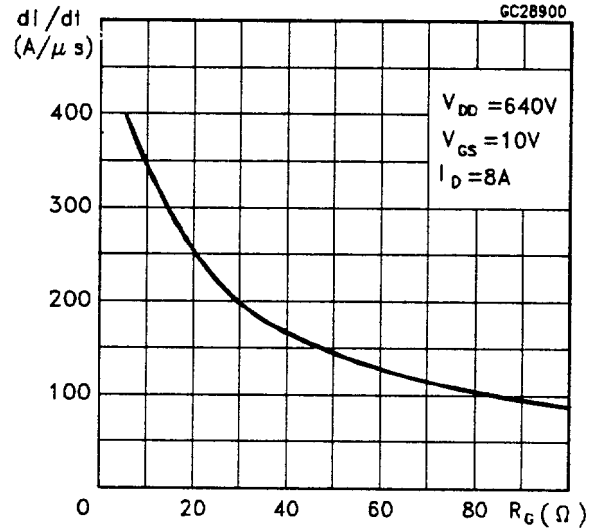
Normalized Gate Threshold Voltage vs Temperature



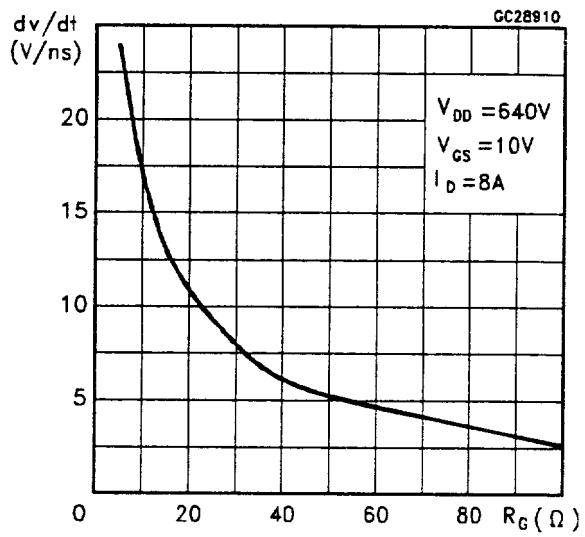
Normalized On Resistance vs Temperature



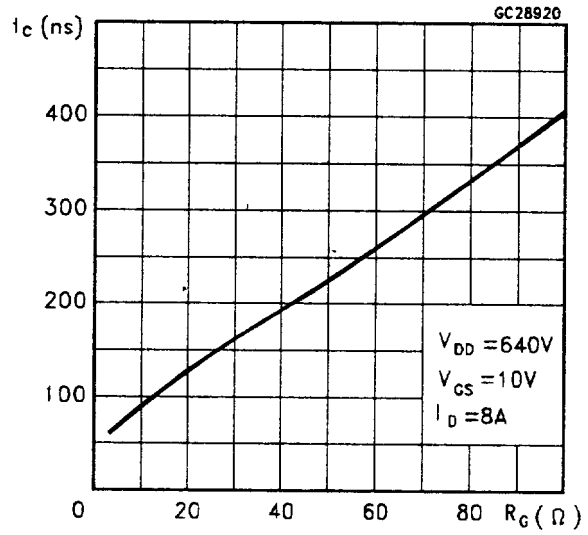
Turn-on Current Slope



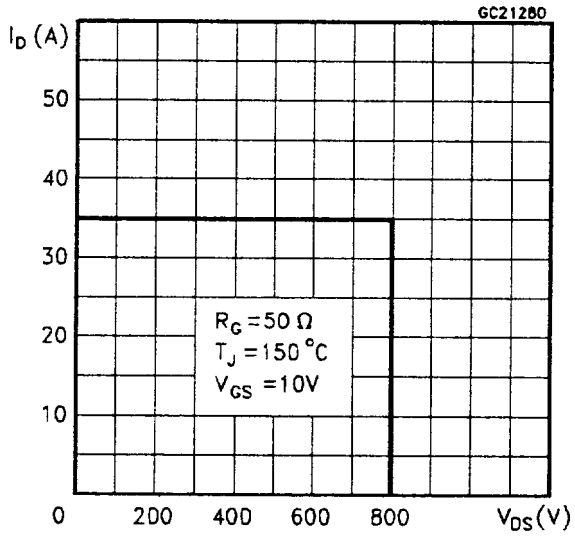
Turn-off Drain-source Voltage Slope



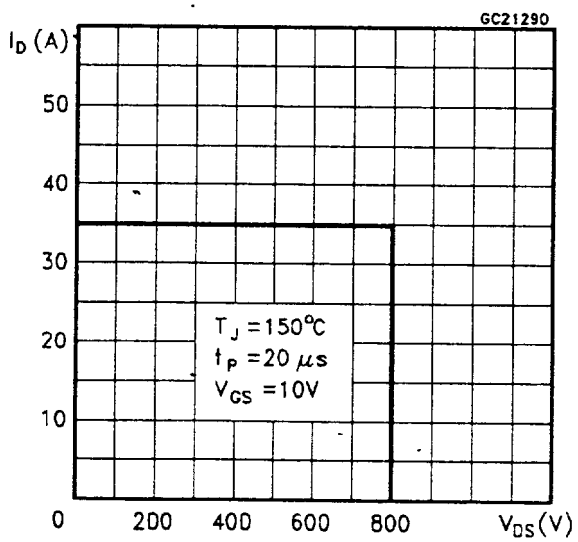
Cross-over Time



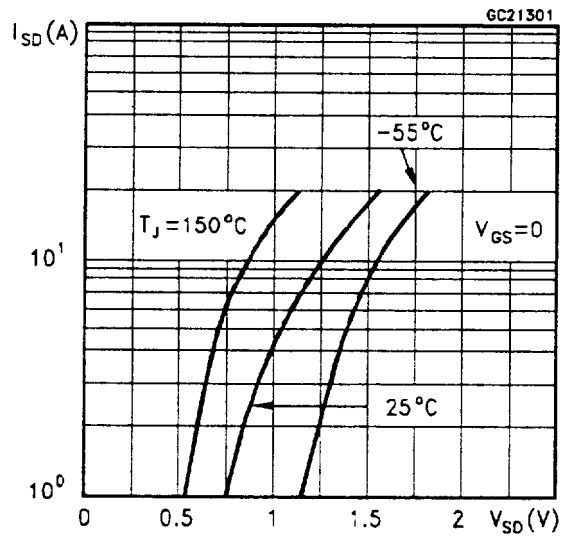
Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics



SGS-THOMSON MICROELECTRONICS

Fig. 1: Unclamped Inductive Load Test Circuits

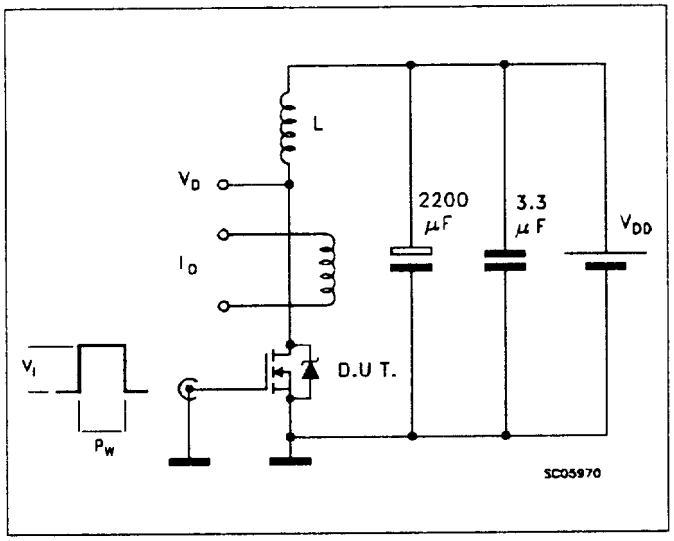


Fig. 2: Unclamped Inductive Waveforms

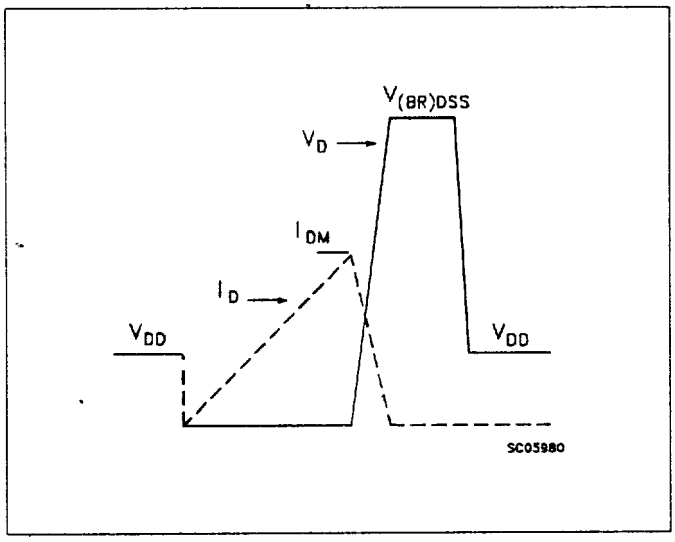


Fig. 3: Switching Times Test Circuits For Resistive Load

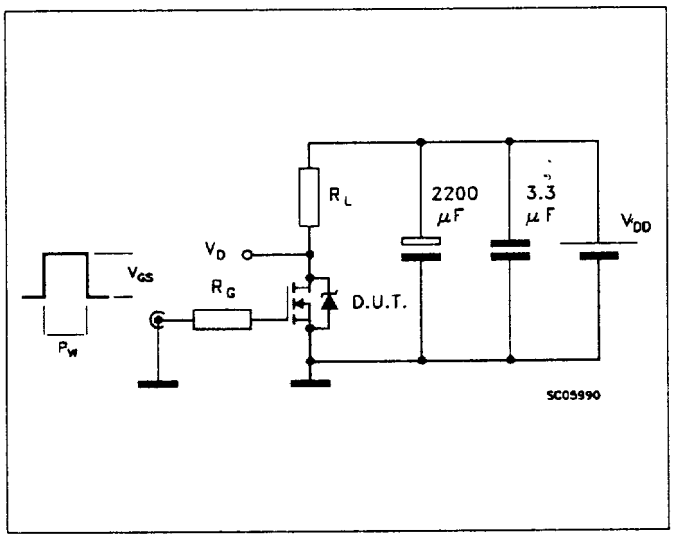


Fig. 4: Gate Charge Test Circuit

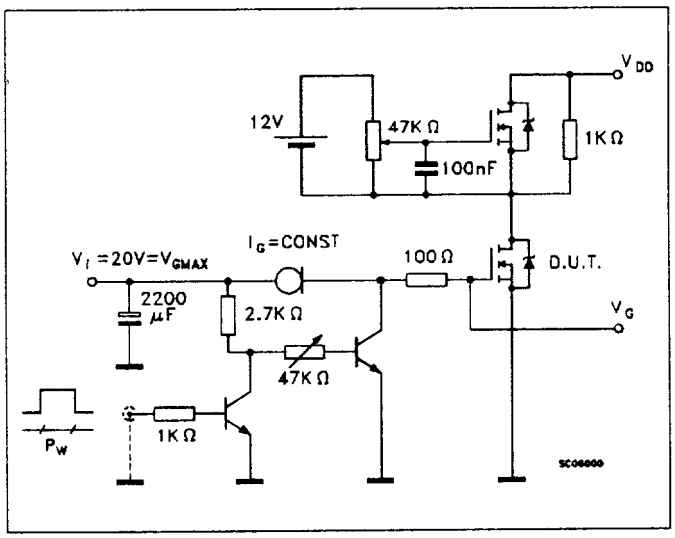


Fig. 5: Test Circuit For Inductive Load Switching And Diode Reverse Recovery Time